

**FEATURES**

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm):  $\varnothing$  4.7
- Peak wavelength:  $\lambda_p = 875$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

**APPLICATIONS**

- Radiation source near infrared range

**DESCRIPTION**

TSTA7300 is an infrared, 875 nm emitting diode in GaAlAs technology in a hermetically sealed TO-18 package with lens.

**PRODUCT SUMMARY**

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSTA7300	20	$\pm 12$	875	600

**Note**

Test conditions see table "Basic Characteristics"

**ORDERING INFORMATION**

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSTA7300	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18

**Note**

MOQ: minimum order quantity

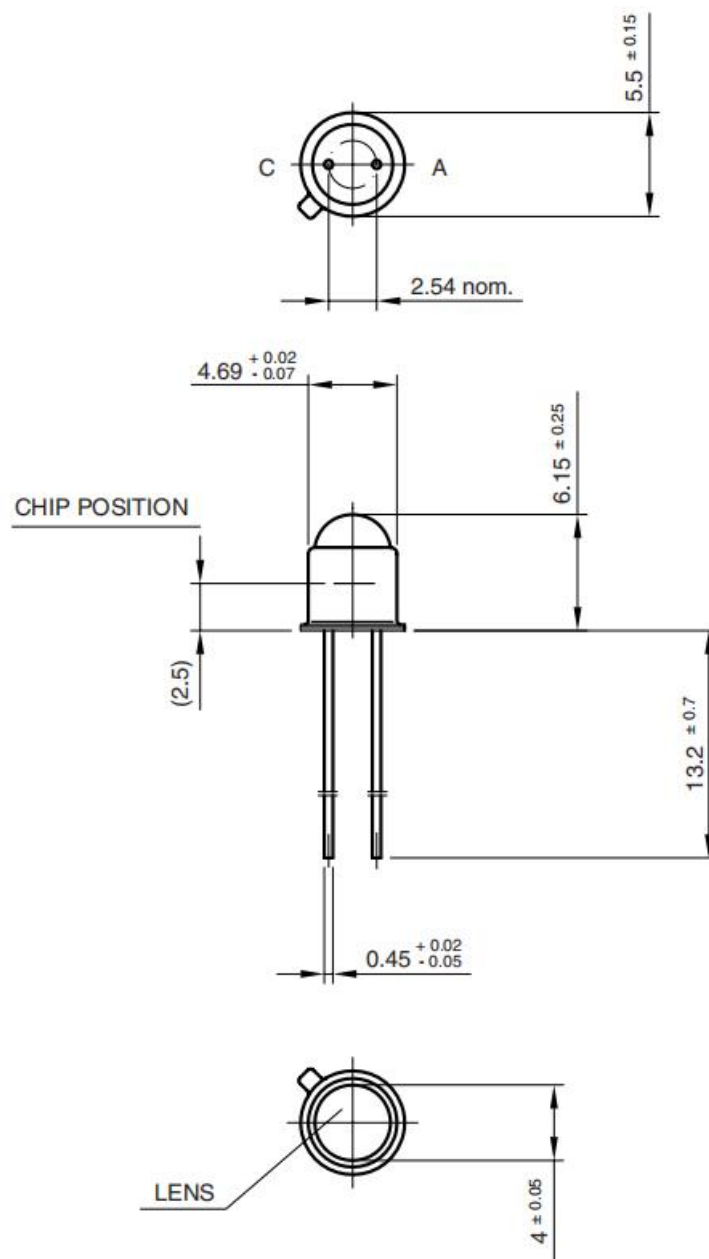
**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p \leq 100 \mu s$	$I_{FM}$	200	mA
Surge forward current	$t_p \leq 100 \mu s$	$I_{FSM}$	2.5	A
Power dissipation		$P_V$	180	mW
	$T_{case} \leq 25^\circ C$	$P_V$	500	mW
Junction temperature		$T_J$	100	$^\circ C$
Storage temperature range		$T_{stg}$	- 55 to + 100	$^\circ C$
Thermal resistance junction/ambient	leads not soldered	$R_{thJA}$	450	K/W
Thermal resistance junction/case	leads not soldered	$R_{thJC}$	150	K/W

**Note**

$T_{amb} = 25^\circ C$ , unless otherwise specified

## PACKAGE DIMENSIONS



### NOTES:

1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25mm(.010") unless otherwise noted.
3. Lead spacing is measured where the leads emerge from the package.

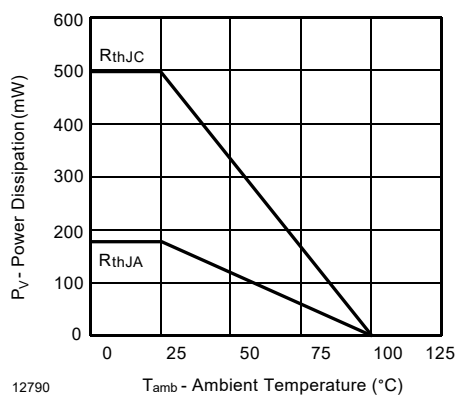


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

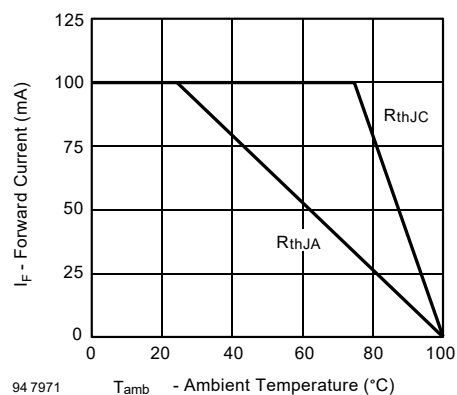


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}$ , $t_p \leq 20 \text{ ms}$	$V_F$		1.4	1.8	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}$	$V_{(BR)}$	5			V
Junction capacitance	$V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $E = 0$	$C_j$		20		pF
Radiant intensity	$I_F = 100 \text{ mA}$ , $t_p \leq 20 \text{ ms}$	$I_e$	10	20	50	mW/sr
Radiant power	$I_F = 100 \text{ mA}$ , $t_p \leq 20 \text{ ms}$	$\phi_e$		10		mW
Temperature coefficient of $\phi_e$	$I_F = 100 \text{ mA}$	$TK\phi_e$		-0.7		%/K
Angle of half intensity		$\varphi$		$\pm 12$		deg
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$		875		nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		80		nm
Rise time	$I_F = 100 \text{ mA}$	$t_r$		600		ns
	$I_F = 1.5 \text{ A}$ , $t_p/T = 0.01$ , $t_p \leq 10 \text{ }\mu\text{s}$	$t_r$		300		ns
Virtual source diameter		$d$		1		mm

**Note**

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**BASIC CHARACTERISTICS**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

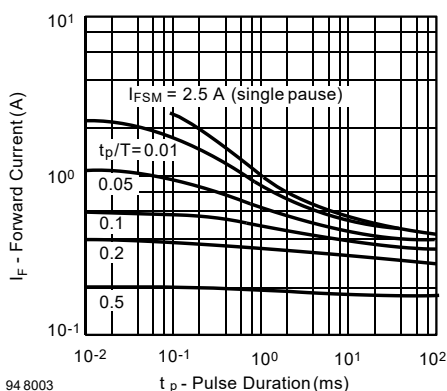


Fig. 3 - Pulse Forward Current vs. Pulse Duration

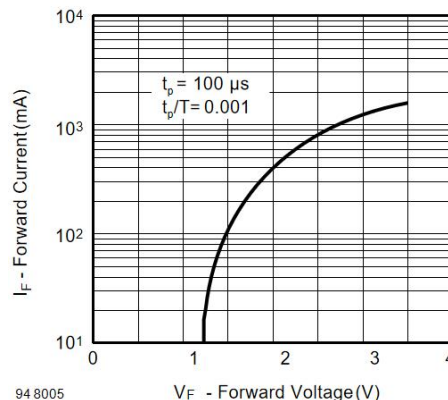


Fig. 4 - Forward Current vs. Forward Voltage

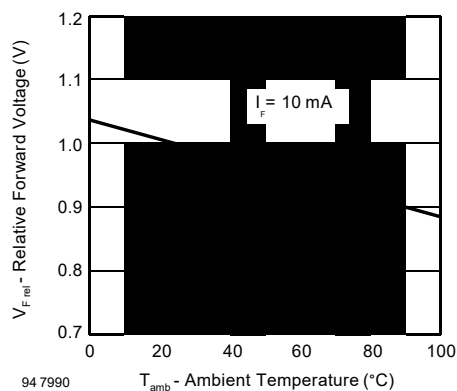


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

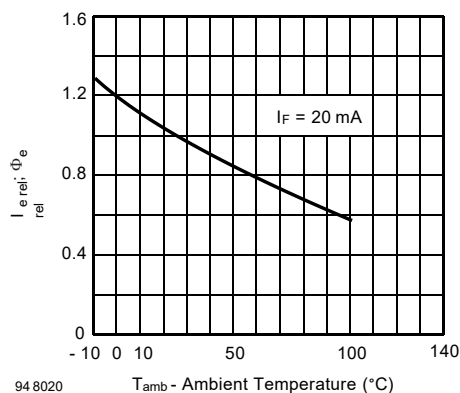


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

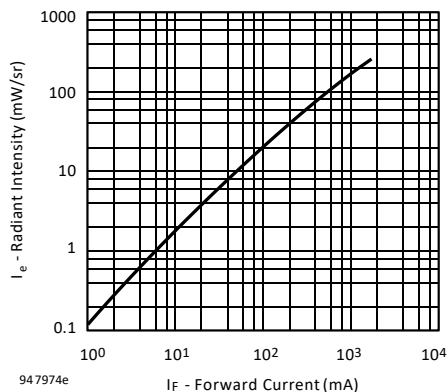


Fig. 6 - Radiant Intensity vs. Forward Current

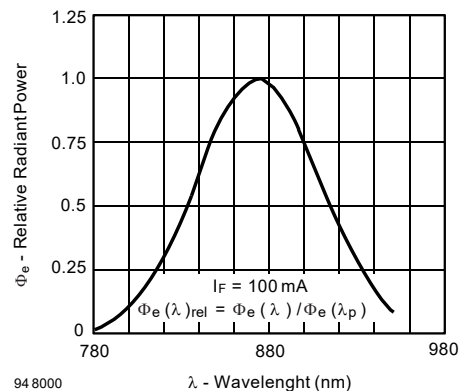


Fig. 9 - Relative Radiant Power vs. Wavelength

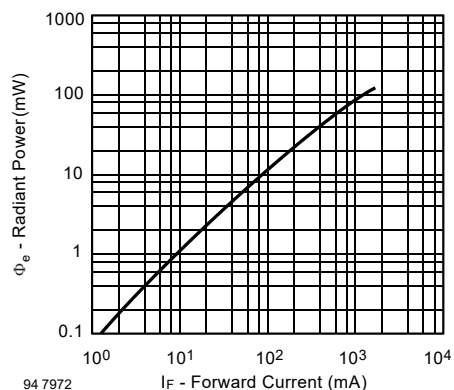


Fig. 7 - Radiant Power vs. Forward Current

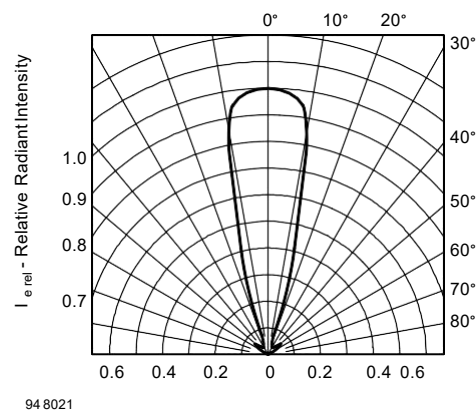


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

**Packing Quantity Specification**

1. 1000Pcs/1Bag,10Bag/1Box
2. 4Boxes/1Carton

**Label Form Specification**

製品名 PRODUCT	
コードNo. CODE No.	
数量 Q'TY	
ロットNo. LOT No.	
備考 REMARKS	
<b>SIVAGO</b> <sup>®</sup> SEMICONDUCTOR	

- PRODUCT: Part Number
- CODE NO.: Product Serial Number
- QTY: Packing Quantity
- LOT No: Lot Number
- REMARKS:Remarks

**Notes****Lead Forming**

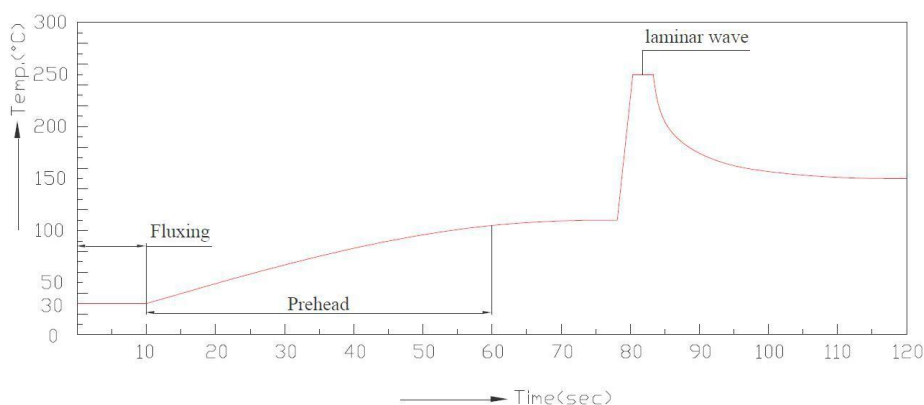
1. During lead formation, the leads should be bent at a point at least 3mm from the base of the epoxy bulb.
2. Lead forming should be done before soldering.
3. Avoid stressing the LED package during leads forming. The stress to the base may damage the LED's characteristics or it may break the LEDs.
4. Cut the LED lead frames at room temperature. Cutting the lead frames at high temperatures may cause failure of the LEDs.
5. When mounting the LEDs onto a PCB, the PCB holes must be aligned exactly with the lead position of the LED. If the LEDs are mounted with stress at the leads, it causes deterioration of the epoxy resin and this will degrade the LEDs.

## Soldering

- Careful attention should be paid during soldering. When soldering, leave more than 3mm from solder joint to epoxy bulb, and soldering beyond the base of the tie bar is recommended.
- Recommended soldering conditions:

Hand Soldering		DIP Soldering	
Temp. at tip of iron	300°C Max. (30W Max.)	Preheat temp.	100°C Max. (60 sec Max.)
Soldering time	3 sec Max.	Bath temp. & time	260 Max., 5 sec Max
Distance	3mm Min.(From solder joint to epoxy bulb)	Distance	3mm Min. (From solder joint to epoxy bulb)

### 3. Recommended soldering profile



- Avoiding applying any stress to the lead frame while the LEDs are at high temperature particularly when soldering.
- Dip and hand soldering should not be done more than one time
- After soldering the LEDs, the epoxy bulb should be protected from mechanical shock or vibration until the LEDs return to room temperature.
- A rapid-rate process is not recommended for cooling the LEDs down from the peak temperature.
- Although the recommended soldering conditions are specified in the above table, dip or hand soldering at the lowest possible temperature is desirable for the LEDs.
- Wave soldering parameter must be set and maintain according to recommended temperature and dwell time in the solder wave.

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